

# Monolithic Amplifier

# TSS-183A+

Mini-Circuits

50 $\Omega$  5 to 18 GHz

#### THE BIG DEAL

- Fast shutdown, 29 nS
- Gain, 13.6 dB typ. & Flatness, ±0.9 dB
- Output Power, up to +17.9 dBm typ.
- Excellent isolation, 36 dB typ.
- Positive Supply Voltage, +5.0V
- Integrated DC blocks, Bias-Tee & Microwave bypass capacitor
- Unconditionally Stable



Generic photo used for illustration purposes only

CASE STYLE: DQ849

+RoHS Compliant The +Suffix identifies RoHS Compliance. See our website for methodologies and qualifications

#### **APPLICATIONS**

- Military EW and Radar
- DBS
- Wideband Isolation amplifier
- Microwave point-to-point radios
- Satellite systems

#### **PRODUCT OVERVIEW**

The TSS-183A+ is a surface mount, MMIC amplifier with shutdown feature fabricated using InGaAs PHEMT technology and is a fully integrated gain block up to 18 GHz. It is packaged in Mini-Circuits industry standard 3x3 mm MCLP package, which provides excellent RF and thermal performance. The TSS-183A+ integrates the entire matching network with the majority of the bias circuit inside the package, reducing the need for complicated external circuits. This approach makes the TSS-183A+ extremely flexible and enables simple, straightforward use.

#### **KEY FEATURES**

Feature	Advantages
Wideband, 5 to 18 GHz	Broad frequency range supports a wide array of applications from microwave radio and radar, to military communica- tions and countermeasures.
Excellent Gain Flatness	Typical ±0.9 dB gain flatness across the entire frequency range minimizes the need for external equalizer networks making it a great fit for instrumentation and EW applications.
High Isolation	With reverse isolation of 36 dB, the TSS-183A+ is an excellent choice for buffering broadband circuits. It is an ideal LO driver amplifier and provides designers system flexibility and margin when integrating cascaded RF components.
Shutdown feature	Allow users to turn on and off the amplifier with pulsed signals while keeping the power supply at constant voltage.
Small size	3x3 mm, 8-lead MCLP package
Integrated DC Blocks & Bias-Tee	Saver motherboard space and minimizes overall cost. Very user friendly.

REV. A ECO-011809 TSS-183A+ MCL NY

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50Ω 5 to 18 GHz

#### ELECTRICAL SPECIFICATIONS<sup>1</sup> AT +25°C, ZO=50Ω, AND V<sub>DD</sub>=+5V UNLESS OTHERWISE NOTED.

Parameter	Condition (GHz)	Amplifier-ON		Amplifier-OFF	Units	
raidifieter	condition (ciriz)	Min.	Тур.	Max.	Тур.	Onits
Frequency Range		5		18	5-18	GHz
	5		7.4		-	
	8		4.1			
Noise Figure	10		4.4			dB
Voise rigure	12		4.6			ub
	14		5.0		-	
	18		6.0		_	
	5	_	13.5	_	-27	
	8	12	14.9	_	-19	
Gain	10	12	14.2	_	-18	dB
	12	—	13.6	_	-17	uв
	14	—	13.4	_	-17	
	18	10.4	13.1	_	-18	
Gain Flatness	5-18		±0.9		_	dB
Reversed Isolation	5-18		36		22	dB
	5		12		6	
	8		36		3	
and Datum Lana	10		16		3	JD
nput Return Loss	12 +		13		4	dB
	14		16		5	
	18		8		5	
	5		9		6	
	8		14		4	
	10		18		4	10
Output Return Loss	12		14		2	dB
	14		13		2	
	18		9		1	
	5	_	+17.2	_	_	
	8	_	+18.5	_	_	
	10	+16.0	+17.9	_		
Output Power @1dB compression AMP-ON	12	_	+17.8	_		dBm
	14	_	+18.7	_		
	18	_	+17.9	_	_	
	5		+33.7		_	
	8		+30.0		_	
Output IP3	10		+28.9		_	
P <sub>out</sub> =+9 dBm/tone)	12		+27.8			dBm
	14		+26.6			
	18		+27.4		_	1
Device Operating Voltage (VDD)		+4.8	+5.0	+5.2	+5.0	V
Device Operating Current (Id)			145	166	0.3	mA
			0	100	-5	V
DC Current (Id) Variation Vs. Temperature <sup>2</sup>			29.4		-	ν μΑ/°C
DC Current (Id) Variation Vs. Voltage			0.0021		_	mA/ C
					-	°C/W
Thermal Resistance Measured on Mini-Circuits Characterization test board			61			°C/W

1 Measured on Mini-Circuits Characterization test board TB-969+. See Characterization Test Circuit (Fig. 1) 2 (Current at  $85^{\circ}$ C - Current at  $-45^{\circ}$ C)/130)



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5 to 18 GHz 50Ω

#### **ABSOLUTE MAXIMUM RATINGS<sup>3</sup>**

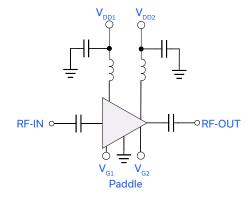
Parameter	Ratings
Operating Temperature (ground lead)	-40°C to +85°C
Storage Temperature	-55°C to +100°C
Total Power Dissipation	0.98 W
Input Power	+20 dBm
DC Voltage $V_{DD}^4$ (Pad 7, 8)	+5.5 V
DC Voltage $V_{G^5}$ (Pad 3, 4)	+-15 V
DC Voltage RF-IN & RF-OUT (Pad 2 & 5)	+10 V

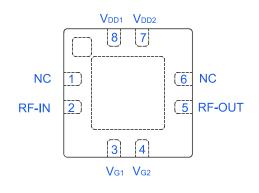
3. Permanent damage may occur if these limits are exceeded. 4. Measured by keeping V<sub>g</sub>=0V. V<sub>DD1</sub>& V<sub>DD2</sub> pads are connected per Figure 1. 5. Measured by keeping V<sub>dd</sub>=5<sub>V,VG1</sub>& V<sub>g2</sub> pads are connected per Figure 1.

#### SWITCHING SPECIFICATIONS (RISE/FALL TIME)

Parameter			Тур.	Max.	Units
Amplifier ON to Shutdown	OFF TIME (50% Control to 10% RF)	-	29 —		
	FALL TIME (90 to 10% RF)	.o 10% RF) —		_	ns
Amplifier Shutdown to ON	ON TIME (50% Control to 90% RF)	-	226	_	
	RISE TIME (10% to 90% RF)	-	163	_	ns
Control Voltage Leakage		-	12	_	mV

#### SIMPLIFIED SCHEMATIC AND PAD DESCRIPTION





Function	Pad Number	Description (See Application Circuit, Fig. 1)
RF-IN	2	RF input pad
RF-OUT	5	RF output pad
$V_{\text{DD1}\&}V_{\text{DD2}}$	7,8	DC power supply (VDD). Two pads are connected per Figure 1.
GND	Paddle	Connected to ground.
$V_{G1\&}V_{G2}$	3,4	Control voltage for shutdown(VG). Two pads are connected per Figure 1.
NC	1,6	No internal connection. Recommended usage per PCB layer PL-588

### CONTROL VOLTAGE (V<sub>c</sub>) FIG. 1

	Min.	Тур.	Max.	Units
Amplifier-ON	-0.2	-	0	V
Amplifier-OFF	-5	_	-4	V

## **Mini-Circuits**



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its 50Ω 5 to 18 GHz

### CHARACTERIZATION TEST CIRCUIT / RECOMMENDED APPLICATION CIRCUIT

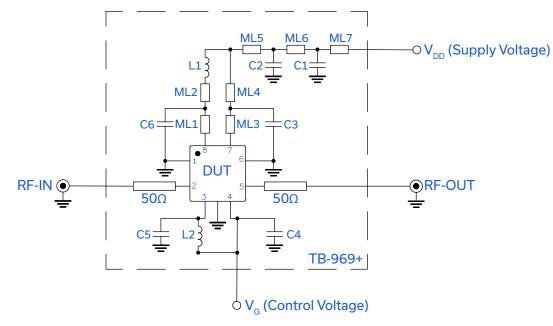


Fig 1. Block diagram of Test Circuit used for characterization. (DUT soldered on Mini-Circuits Characterization test board TB-969+) Gain, Return loss, Output power at 1dB compression (P1dB), output IP3 (OIP3) and noise figure measured using Agilent's N5242A PNA-X microwave network analyzer.

Conditions:

1. Gain and Return loss:  $P_{IN}$ = -25dBm

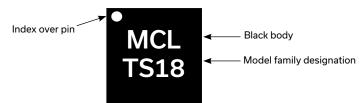
2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, +9dBm/tone at output.

3. Switching Time: P<sub>IN</sub>=7dBm at 5.2 GHz. VG=Pulse signal at 1 KHz, -5V, with offset=-2.5V, 50% duty cycle. Vdd=5V.

Component	P/N	Supplier	Value	Size
C1	GRM1555C1H5R6CA01D	Murata	5.6pF	0402
C2	GRM1555C1H180JA01D	Murata	18pF	0402
C3 – C5	GRM1555C1H102JA01D	Murata	0.001uF	0402
C6	GRM155R71C104KA88D	Murata	0.1uF	0402
L1 , L2	0805CS-030XJLC	Coilcraft	3.3nH	0805

ML1 to ML7 are short mircrostrip lines. Refer to PL-588

#### **PRODUCT MARKING**



Marking may contain other features or characters for internal lot control



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### ADDITIONAL DETAILED TECHNICAL INFORMATION IS AVAILABLE ON OUR DASHBOARD. CLICK HERE

Performance Data	Data Table Swept Graphs S-Parameter (S2P Files) Data Set (.zip file)
Case Style	DQ849 Plastic package, exposed paddle, lead finish: matte-tin
Tape & Reel Standard quantities available on reel	F104 7" reels with 20, 50, 100, 200, 500, 1K, or 2K devices
Suggested Layout for PCB Design	PL-588
Evaluation Board	TB-969+
Environmental Ratings	ENV08T1

#### **ESD RATING**

Human Body Model (HBM): 1A (250 to <500V) in accordance with ANSI/ESD STM 5.1 - 2001

NOTES

A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.

B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.

C. The parts covered by this specification document are subject to Mini-Circuits standard limited warranty and terms and conditions (collectively, "Standard Terms"); Purchasers of this part are entitled to the rights and benefits contained therein. For a full statement of the standard terms and the exclusive rights and remedies thereunder, please visit Mini-Circuits' website at <a href="http://www.minicircuits.com/terms/viewterm.html">www.minicircuits.com/terms/viewterm.html</a>

